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THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Masanobu ANDO, et al.

Serial No.:	10/564,416	Group Art Unit:	Not Yet Assigned
Filing Date:	January 12, 2006	Examiner:	Not Yet Assigned

For: LIGHT-EMITTING SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING IT.

Honorable Commissioner of Patents
Alexandria, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Under the provisions of 37 CFR §1.97 through §1.98 and pursuant to Applicants' duty of disclosure under 37 CFR §1.56, Applicants respectfully bring the following documents cited in the European Search Report in a counterpart foreign application and listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application.

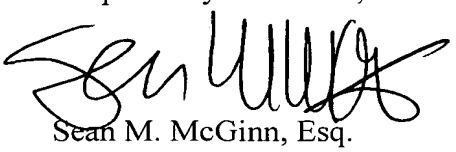
This citation does not constitute an admission that the references are relevant or material to the claims. They are only cited as constituting related art of which Applicants are aware.

In compliance with the concise explanation requirement under 37 CFR §1.98(a)(3) for foreign language documents, Applicants enclose herewith a copy of the European Search Report citing such documents, together with an English-language version (if not already included) of that portion of the Search Report indicating the degree of relevance found by the foreign office.

I hereby certify that each item of information contained in this Information Disclosure Statement was the first citation of that item by a foreign patent office in a counterpart foreign application, which occurred not more than three months prior to the filing of this statement.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Respectfully submitted,



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INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
F05-420-US	10/564,416
Applicant(s)	
Masanobu ANDO, et al.	
Filing Date	**Group Art Unit**
January 12, 2006	Not Yet Assigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		2002/0171092 A1	11/21/2002	GOETZ, et al.			

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO
		EP 1 280 212 A2	01/29/2003	Europe				
		0 662 739 A1	07/12/1995	Europe				
		11-026812	01/29/1999	Japan			ABS ONLY	

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

		European Search Report dated March 8, 2006

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

		Kneissl, et al. "Continuous-wave operation of ultraviolet InGaN/InAlGaN multiple-quantum-well laser diodes", Applied Physics Letters, AIP, American Institute of Physics, Melville, NY, US, Vol. 82, No. 15, April 14, 2003, Pages 2386-2388, XP012033738.
		Nakamura, et al. " InGaN/GaN/AlGaN-based laser diodes with modulation-doped strained-layer superlattices grown on an epitaxially laterally overgrown GaN substrate", Applied Physics Letter, AIP, American Institute of Physics, Melville, NY, US, Vol. 72, No. 2, January 12, 1998.

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